

**AMENDMENTS TO THE CLAIMS**

Please cancel claims 1-13 and 15 without prejudice or disclaimer of their underlying subject matter.

Please amend the claims as follows.

1-13. (canceled)

14. (currently amended) ~~The A~~ thin film semiconductor device ~~according to Claim 13~~ comprising:

an insulating substrate; and

a thin film transistor formed on said insulating substrate, wherein:

said thin film transistor is formed in a bottom gate structure having gate electrode, a gate insulating film, and a semiconductor thin film stacked in the order from below upward,

said gate electrode is made of metallic material having a thickness of less than 100nm,

said gate insulating film has a thickness that is greater than said thickness of said gate electrode,

the thickness of the gate insulating film is greater than 100 nm, and

~~wherein~~ the thickness of the gate insulating film is 110 nm and the thickness of the gate electrode is 90 nm.

15. (canceled)

16. (currently amended) ~~The A~~ display device ~~according to Claim 15~~ comprising:

an insulating substrate;

pixels arranged in a matrix form;

thin film transistors for driving said respective pixels, wherein said pixels and said thin film transistors are formed as integrated circuits on said insulating substrate, each of said thin film transistors has a bottom gate structure having a gate electrode, a gate insulating film and a semiconductor thin film stacked in the order from below upward, and

said gate electrode is made of metallic material having a thickness of less than 100 nm,

said gate insulating film has a thickness that is greater than said thickness of said gate electrode,

wherein the thickness of the gate insulating film is greater than 100 nm, and

wherein the thickness of the gate insulating film is 110 nm and the thickness of the gate electrode is 90 nm.